

INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>	Docket Number (Optional) TWI-11220	Application Number NEW 10/691,132
	Applicant(s) Jon Opsal et al.	
	Filing Date HEREWITH	Group Art Unit Unknown 2877

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE
	*AA	4,634,290	01/06/1987	Rosencwaig et al.	374	5	11/14/1985
	*AB	4,636,088	01/13/1987	Rosencwaig et al.	347	5	05/21/1984
	*AC	4,854,710	08/08/1989	Opsal et al.	356	432	07/23/1987
	*AD	4,999,014	03/12/1991	Gold et al.	356	382	05/04/1989
	*AE	5,074,669	12/24/1991	Opsal	356	445	12/12/1989
	*AF	5,181,080	01/19/1993	Fanton et al.	356	381	12/23/1991
	*AG	5,206,710	04/27/1993	Geiler et al.	356	432	09/25/1991
	*AH	5,536,936	07/16/1996	Drevillon et al.	250	226	01/11/1995
	*AI	5,798,837	08/25/1998	Aspnes et al.	356	369	07/11/1997
	*AJ	5,900,939	05/04/1999	Aspnes et al.	356	243.1	06/17/1998
	*AK	5,953,446	09/14/1999	Opsal et al.	382	141	10/09/1998
	*AL	5,973,787	10/26/1999	Aspnes et al.	356	369	05/12/1998
	*AM	5,978,074	11/02/1999	Opsal et al.	356	72	07/03/1997
	*AN	6,008,906	12/28/1999	Maris	250	226	09/05/1997
	*AO	6,128,084	10/03/2000	Nanbu et al.	356	369	06/10/1998
	*AP	6,191,846	02/20/2001	Opsal et al.	356	364	11/01/1999
	*AQ	6,268,916	07/31/2001	Lee et al.	356	369	05/11/1999
	*AR	6,278,519	08/21/2001	Rosencwaig et al.	250	225	01/29/1998
	*AS	6,535,285	08/18/2003	Opsal et al.	356	369	02/08/2000


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*AV	M. Fried et al., "Nondestructive determination of damage depth profiles in ion-implanted semiconductors by spectroscopic ellipsometry using different optical models," <i>J. Appl. Phys.</i> , Vol. 71, No. 6, 15 March 1992, pp. 2835-2843.
*AW	A.P. Webb et al., "Refractive index profiles induced by ion implantation into silica," <i>J. Phys. D: Appl. Phys.</i> , Vol. 9, 1976, pp. 1343-1354.
*AX	J.R. Adams, "Complex refractive index and phosphorus concentration profiles in P31 ion implanted silicon by ellipsometry and auger electron spectroscopy," <i>Surface Science</i> , Vol. 56, 1976, pp. 307-311.
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*AZ	J.P. Cortot et al., "Analysis of arsenic and phosphorus ion implanted silicon by spectroscopic ellipsometry," <i>Appl. Phys. Lett.</i> , Vol. 41, No. 1, 1 July 1982, pp. 93-95.
*BA	X-F. He et al., "Disorder effects on optical spectra and band structure of Si induced by ion implantation," <i>J. Appl. Phys.</i> , Vol. 66, No. 11, 1 December 1989, pp. 5261-5266.
*BB	T. Yamaguchi et al., "Empirical dielectric function of amorphous materials for spectroscopic ellipsometry," <i>J. Appl. Phys.</i> , Vol. 77, No. 9, 1 May 1995, pp. 4673-4676.
*BC	Kravetsky, Kulyuk et al., "Reflected optical second harmonic generation as a method for characterization of ion-implanted, thermal annealed silicon surfaces and silicon-insulator interfaces," <i>Ion Implanted Technology</i> , Vol. 94, 1995, pp. 656-659.

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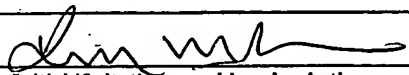
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*BE	Y. Yakeda et al., "Large third-order optical nonlinearity of tin microcrystallite-doped silica glass formed by ion implantation," <i>Appl. Phys. Lett.</i> , Vol. 63, No. 25, 20 December 1993, pp. 3420-3422.
*BF	J.W.C. England et al., "The dynamics of amorphous-to-crystalline interface evolution in ion-implanted polycrystalline silicon," <i>J. Appl. Phys.</i> , Vol. 73, No. 9, 1 May 1993, pp. 4332-4343.
*BG	E. Chason et al., "In situ energy dispersive x-ray reflectivity measurements of H ion bombardment on SiO ₂ /Si and Si," <i>Appl. Phys. Lett.</i> , Vol. 60, No. 19, 11 May 1992, pp. 2353-2355.
*BH	Y.Z. Hu et al., "A Comparison of Argon and Hydrogen Ion Etching and Damage in the Si-SiO ₂ System," <i>J. Electrochem. Soc.</i> , Vol. 139, No. 7, July 1992, pp. 2022-2026.
*BI	R.E. Hummel et al., "Ion Implantation Damage and Annealing of Silicon as Characterized by Differential Reflectometry," <i>J. Electrochem. Soc.</i> , Vol. 137, No. 11, November 1990, pp. 3583-3588.
*BJ	N.V. Nguyen et al., "Spectroscopic ellipsometry studies of crystalline silicon implanted with carbon ions," <i>J. Appl. Phys.</i> , Vol. 67, No. 8, 15 April 1990, pp. 3555-3559.
*BK	G.F. Feng et al., "Optical properties of ion-implanted GaAs: The observation of finite-size effects in GaAs microcrystals," <i>Physical Review B</i> , Vol. 40, No. 2, 15 July 1989, pp. 1064-1073.
*BL	L. Chen et al., "Transient photomodulation spectroscopy of amorphous hydrogenated silicon," <i>Physical Review B</i> , Vol. 39, No. 8, 15 March 1989, pp. 5121-5127.
*BM	A.H.M. Holtslag et al., "Noble-gas ion bombardment on clean silicon surfaces," <i>Physical Review B</i> , Vol. 38, No. 15, 15 November 1988, pp. 10556-10570.
*BN	R.E. Hummel et al., "Optical investigations of ion implant damage in silicon," <i>J. Appl. Phys.</i> , Vol. 63, No. 8, 15 April 1988, pp. 2591-2594.
*BO	J.L. Buckner et al., "Ellipsometric and Rutherford backscattering characterization of low-energy hydrogen-, helium-, neon-, and argon-bombarded silicon," <i>J. Appl. Phys.</i> , Vol. 63, No. 11, 1 June 1988, pp. 5288-5294.
*BP	J. Narayan et al., "Formation and nondestructive characterization of ion implanted silicon-on-insulator layers," <i>Appl. Phys. Lett.</i> , Vol. 51, No. 5, 3 August 1987, pp. 343-345.
*BQ	P.J. McMarr et al., "Spectroscopic ellipsometry: A new tool for nondestructive depth profiling and characterization of interfaces," <i>J. Appl. Phys.</i> , Vol. 59, No. 3, 1 February 1986, pp. 694-701.
*BR	X.C. Mu et al., "Ar ion beam and CCl ₄ reactive ion etching: A comparison of etching damage and of damage passivation by hydrogen," <i>J. Appl. Phys.</i> , Vol. 58, No. 11, 1 December 1985, pp. 4282-4291.
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*BT	K. Vedam et al., "Nondestructive depth profiling by spectroscopic ellipsometry," <i>Appl. Phys. Lett.</i> , Vol. 47, No. 4, 15 August 1985, pp. 339-341.

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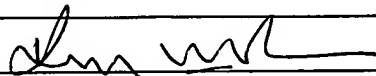
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*BU	M. Erman et al., "Analysis of ion-implanted GaAs by Spectroscopic ellipsometry," <i>Surface Science</i> , Vol. 135, 1983, pp. 353-373.
*BV	J.B. Theeten et al., "Depth profiling and interface analysis using spectroscopic ellipsometry," <i>J. Vac. Sci. Technol.</i> , Vol. 20, No. 3, March 1982, pp. 471-475.
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*BX	D.E. Aspnes et al., "Direct Determination of States of Excitations from Optical Measurements on Ion-Implanted GaAs," <i>Physical Review Letters</i> , Vol. 48, No. 26, 28 June 1982, pp. 1863-1866.
*BY	Q. Kim & Y.S. Park, "Ellipsometric investigation of ion-implanted GaAs," <i>Surface Science</i> , Vol. 96, 1980, pp. 307-318.
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*CA	D.E. Aspnes et al., "An investigation of ion-bombarded and annealed (111) surfaces of Ge by spectroscopic ellipsometry," <i>Surface Science</i> , Vol. 96, 1980, pp. 294-306.
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*CC	V.V. Galkin et al., "Implantation of 10-80 keV lithium ions in diamond," <i>Soviet Physics - Semiconductors</i> , Vol. 4, No. 5, November 1970, pp. 709-716.
*CD	V.V. Galkin et al., "Ion-bombardment induced damage in diamond layers," <i>Soviet Physics - Solid State</i> , Vol. 10, No. 3, September 1968, pp. 706-708.
*CE	J.M. Leng et al., "Simultaneous measurement of six layers in a silicon on insulator film stack using spectrophotometry and beam profile reflectometry," <i>J. Appl. Phys.</i> , Vol. 81, No. 8, 15 April 1997, pp. 3570-3578.
*CF	U Zammit et al., "Optical absorption in ion implanted Si films," <i>Nuclear Instruments and Methods in Physics Research B</i> , Vol. 96, 1995, pp. 241-244.
*CG	A. Rosencwaig et al., "Thermal wave characterization of semiconductors and superconductors," <i>Review of Progress in Quantitative Nondestructive Evaluation</i> , Vol 8B, 1989, pp. 1195-1201.
*CH	J. Opsal, "Modulated interference effects and thermal wave monitoring of high-dose ion implantation in semiconductors," <i>Review of Progress in Quantitative Nondestructive Evaluation</i> , Vol 8B, 1989, pp. 1241-1245.
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